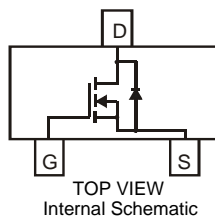


## Features

- Low On-Resistance
  - 150 mΩ @V<sub>GS</sub> = 4.5V
  - 200 mΩ @V<sub>GS</sub> = 2.5V
  - 240 mΩ @V<sub>GS</sub> = 1.8V
  - 300 mΩ @V<sub>GS</sub> = 1.5V
- Ultra Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 3 and 5)
- Qualified to AEC-Q101 Standards for High Reliability



SOT-23



## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	30	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Drain Current (Note 1)	I <sub>D</sub>	2.0	A
Pulsed Drain Current (Note 1)	I <sub>DM</sub>	8	A

## Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P <sub>D</sub>	600	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	208	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 4)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	37	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 100μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 4)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	—	1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	100	150	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.5A
			140	200		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.5A
			185	250		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 1.5A
			240	300		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 0.5A
			—	—		—
Forward Transfer Admittance	Y <sub>fs</sub>	—	5	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.4A
Diode Forward Voltage (Note 4)	V <sub>SD</sub>	—	0.8	1.1	V	V <sub>GS</sub> = 0V, I = 0.5A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	193	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	35	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	23	—	pF	
Turn-On Delay Time	t <sub>d(on)</sub>	—	7	—	ns	V <sub>DD</sub> = 10V, R <sub>L</sub> = 10Ω I <sub>D</sub> = 1A, V <sub>GEN</sub> = 4.5V, R <sub>G</sub> = 6Ω
Rise Time	t <sub>r</sub>	—	24	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	24	—		
Fall Time	t <sub>f</sub>	—	12	—		

- Notes:
1. Device mounted on FR-4 PCB.
  2. No purposefully added lead. Halogen and Antimony Free.
  3. Detail go to our website at [www.twtysemi.com](http://www.twtysemi.com)
  4. Short duration pulse test used to minimize self-heating effect.
  5. Product manufactured with Green Molding Compound and does not contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.